

# SN74LV595A-Q1 具有三态输出寄存器的 8 位移位寄存器

## 1 特性

- 符合汽车应用要求
- 采用具有可湿性侧面的 QFN (WBQB) 封装
- 可支持客户特殊配置控制与重大变更批准
- 2V 至 5.5V  $V_{CC}$  运行
- $V_{CC} = 3.3V$ 、 $T_A = 25^\circ C$  时,  $V_{OLP}$  (输出接地反弹) 典型值小于 0.8V
- $V_{CC} = 3.3V$ 、 $T_A = 25^\circ C$  时,  $V_{OHV}$  (输出  $V_{OH}$  下冲) 典型值大于 2.3V
- 所有端口上均支持以混合模式电压运行
- 8 位串行输入/并行输出移位寄存器
- $I_{off}$  支持局部断电模式运行
- 移位寄存器具有直接清零功能

## 2 应用

- 输出扩展
- LED 矩阵控制
- 7 段显示控制

## 3 说明

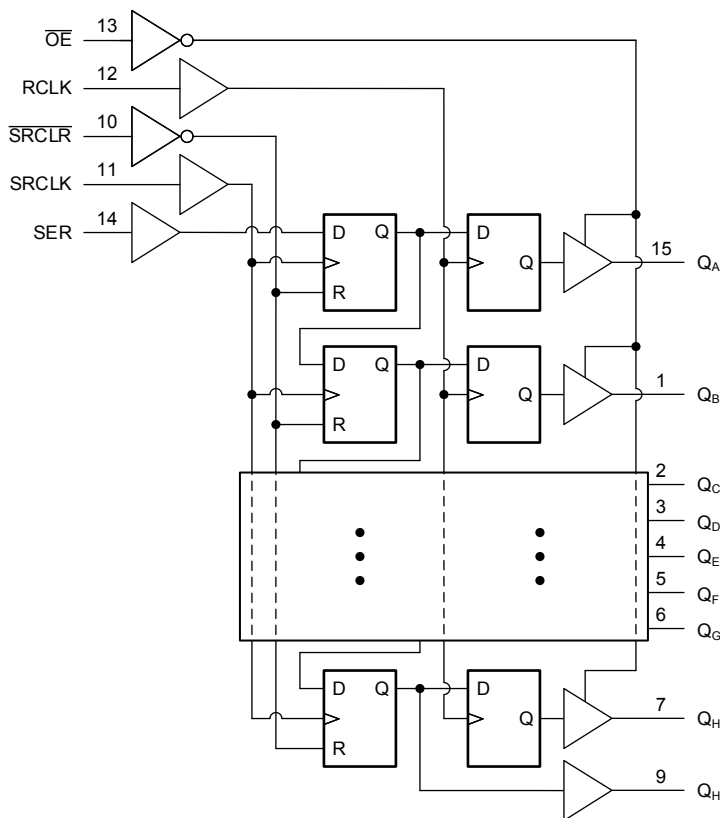
SN74LV595A-Q1 包含一个对 8 位 D 类存储寄存器进行馈送的 8 位串行输入、并行输出移位寄存器。存储寄存器具有并行三态输出。移位寄存器和存储寄存器分别有单独的时钟。移位寄存器具有一个直接覆盖清零 (SRCLR) 输入以及用于级联结构的串行 (SER) 输入和串行输出。当输出使能端 ( $\overline{OE}$ ) 输入为高电平时, 所有输出 ( $Q_H$  除外) 处于高阻抗状态。

该器件完全符合使用  $I_{off}$  的部分断电应用的规范要求。 $I_{off}$  电路禁用输出, 从而可防止其断电时破坏性电流从该器件回流。

### 封装信息<sup>(1)</sup>

器件型号	封装	封装尺寸 (标称值)
SN74LV595A-Q1	PW (TSSOP, 16)	5.00mm × 4.40mm
	WBQB (WQFN, 16)	3.60mm × 2.60mm

(1) 如需了解所有可用封装, 请参阅数据表末尾的可订购产品附录。



逻辑图 (正逻辑)

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## 4 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision F (November 2022) to Revision G (March 2023)	Page
• 根据当前标准更新了文档的结构布局.....	1
• Updated thermal values for PW package from $R^{\theta}_{JA} = 108$ to 138.7, $R^{\theta}_{JC(top)} = 40.8$ to 69.1, $R^{\theta}_{JB} = 51.1$ to 81.8, $\Psi_{JT} = 3.8$ to 20.3, $\Psi_{JB} = 50.6$ to 81.3, all values in $^{\circ}\text{C/W}$ .....	5

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Changes from Revision E (June 2022) to Revision F (November 2022)	Page
• 将数据表的状态从 <i>预告信息</i> 更改为 <i>量产数据</i> .....	1

## 5 Pin Configuration and Functions

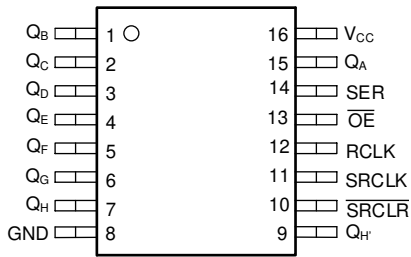


图 5-1. PW Package,  
16-Pin TSSOP  
(Top View)

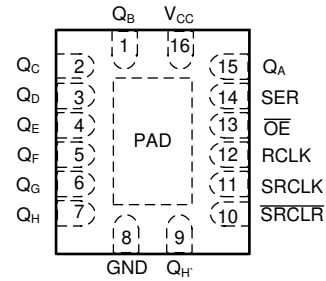


图 5-2. WBQB Package,  
16-Pin WQFN  
Transparent (Top View)

表 5-1. Pin Functions

PIN		TYPE <sup>(1)</sup>	DESCRIPTION
NAME	NO.		
GND	8	G	Ground
$\overline{OE}$	13	I	Output Enable Pin
QA	15	O	QA Output
QB	1	O	QB Output
QC	2	O	QC Output
QD	3	O	QD Output
QE	4	O	QE Output
QF	5	O	QF Output
QG	6	O	QG Output
QH	7	O	QH Output
QH'	9	O	QH' Output
SRCLR	10	I	SRCLR Input
SRCLK	11	I	SRCLK Input
RCLK	12	I	RCLK Input
SER	14	I	SER Input
V <sub>CC</sub>	16	P	Positive Supply
PAD	—	—	Thermal Pad <sup>(2)</sup>

(1) I = Input, O = Output, I/O = Input or Output, G = Ground, P = Power.

(2) WBQB Package Only

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage range	- 0.5	7.0	V
V <sub>I</sub>	Input voltage range <sup>(2)</sup>	- 0.5	7.0	V
V <sub>O</sub>	Voltage range applied to any output in the high-impedance or power-off state <sup>(2)</sup>	- 0.5	4.6	V
	Output voltage range applied to any output in the high or low state <sup>(2) (3)</sup>	- 0.5	V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	Input clamp current <sup>(2)</sup>	V <sub>I</sub> < 0		- 20 mA
I <sub>OK</sub>	Output clamp current <sup>(2)</sup>	V <sub>O</sub> < 0		-50 mA
I <sub>O</sub>	Continuous output current			±35 mA
	Continuous current through V <sub>CC</sub> or GND			±70 mA
T <sub>J</sub>	Junction temperature			150 °C
T <sub>stg</sub>	Storage temperature	- 65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) The package thermal impedance is calculated in accordance with JESD 51-7.

### 6.2 ESD Ratings

		VALUE	UNIT
V <sub>(ESD)</sub>	Electrostatic discharge	Human-body model (HBM), per AEC Q100-002 HBM ESD Classification Level 2 <sup>(1)</sup>	
		±2000	V
		Machine Model (MM), per JEDEC specification	
	±200		
	Charged-device model (CDM), per AEC Q100-011 CDM ESD Classification Level C4B		±1000

- (1) AEC Q100-002 indicate that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

### 6.3 Recommended Operating Conditions

		MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage	2	5.5	V
V <sub>IH</sub>	High-level input voltage	V <sub>CC</sub> = 2 V	1.5	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	V <sub>CC</sub> × 0.7	
		V <sub>CC</sub> = 3 V to 3.6 V	V <sub>CC</sub> × 0.7	
		V <sub>CC</sub> = 4.5 V to 5.5 V	V <sub>CC</sub> × 0.7	
V <sub>IL</sub>	Low-level input voltage	V <sub>CC</sub> = 2 V	0.5	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	V <sub>CC</sub> × 0.3	
		V <sub>CC</sub> = 3 V to 3.6 V	V <sub>CC</sub> × 0.3	
		V <sub>CC</sub> = 4.5 V to 5.5 V	V <sub>CC</sub> × 0.3	
V <sub>I</sub>	Input voltage <sup>(1)</sup>	0	5.5	V
V <sub>O</sub>	Output voltage	High or low state	0	V <sub>CC</sub>
		3-state	0	5.5
I <sub>OH</sub>	High level output current	V <sub>CC</sub> = 2 V	-50	μA
		V <sub>CC</sub> = 2.3 V to 2.7 V	-2	mA
		V <sub>CC</sub> = 3 V to 3.6 V	-8	
		V <sub>CC</sub> = 4.5 V to 5.5 V	-16	
I <sub>OL</sub>	Low level output current	V <sub>CC</sub> = 2 V	50	μA
		V <sub>CC</sub> = 2.3 V to 2.7 V	2	mA
		V <sub>CC</sub> = 3 V to 3.6 V	8	
		V <sub>CC</sub> = 4.5 V to 5.5 V	16	
Δt / Δv	Input transition rise/fall time	V <sub>CC</sub> = 2.3 V to 2.7 V	200	ns/V
		V <sub>CC</sub> = 3 V to 3.6 V	100	
		V <sub>CC</sub> = 4.5 V to 5.5 V	20	
T <sub>A</sub>	Operating free-air temperature	SN74LV595AIPWRQ1	-40	85
		SN74LV595AQPWRQ1 or SN74LV595AQWBQRQ1	-40	125

(1) All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. See the TI application report, [Implications of Slow or Floating CMOS Inputs](#).

### 6.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		SN74LV595A-Q1		UNIT
		PW (TSSOP)	WBQB (WQFN)	
		16 PINS	16 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	138.7	86	°C/W
R <sub>θJC(top)</sub>	Junction-to-case (top) thermal resistance	69.1	82.6	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	81.8	54.9	°C/W
Ψ <sub>JT</sub>	Junction-to-top characterization parameter	20.3	9.5	°C/W
Ψ <sub>JB</sub>	Junction-to-board characterization parameter	81.3	54.9	°C/W
R <sub>θJC(bot)</sub>	Junction-to-case (bottom) thermal resistance	N/A	32.5	°C/W

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).

## 6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V <sub>CC</sub>	- 40°C to 85°C			- 40°C to 125°C			UNIT	
				MIN	TYP	MAX	MIN	TYP	MAX		
V <sub>OH</sub>		I <sub>OH</sub> = - 50 μA	2 V to 5.5 V	V <sub>CC</sub> - 0.1			V <sub>CC</sub> - 0.1			V	
		I <sub>OH</sub> = - 2 mA	2.3 V	2			2				
	Q <sub>H</sub> '	I <sub>OH</sub> = - 6 mA	3 V	2.48			2.45				
	Q <sub>A</sub> - Q <sub>H</sub>	I <sub>OH</sub> = - 8 mA		2.48			2.45				
	Q <sub>H</sub> '	I <sub>OH</sub> = - 12 mA	4.5 V	3.8			3.7				
	Q <sub>A</sub> - Q <sub>H</sub>	I <sub>OH</sub> = - 16 mA		3.8			3.7				
V <sub>OL</sub>		I <sub>OL</sub> = 50 μA	2 V to 5.5 V				0.1			V	
		I <sub>OL</sub> = 2 mA	2.3 V				0.4				
	Q <sub>H</sub> '	I <sub>OL</sub> = 6 mA	3 V				0.44				
	Q <sub>A</sub> -Q <sub>H</sub>	I <sub>OL</sub> = 8 mA					0.44				
	Q <sub>H</sub> '	I <sub>OL</sub> = 12 mA	4.5 V				0.55				
	Q <sub>A</sub> -Q <sub>H</sub>	I <sub>OL</sub> = 16 mA					0.55				
I <sub>I</sub>	V <sub>I</sub> = 5.5 V or GND		0 to 5.5 V				±1			μA	
I <sub>OZ</sub>	Q <sub>A</sub> - Q <sub>H</sub>	V <sub>O</sub> = V <sub>CC</sub> or GND,	5.5 V				±5			±10	μA
I <sub>CC</sub>	V <sub>I</sub> = V <sub>CC</sub> or GND, I <sub>O</sub> = 0		5.5 V				20			40	μA
I <sub>off</sub>	V <sub>I</sub> or V <sub>O</sub> = 0 to 5.5 V		0 V				5			10	μA
C <sub>i</sub>	V <sub>I</sub> = V <sub>CC</sub> or GND		3.3 V	3.5			3.5			pF	

## 6.6 Timing Requirements, V<sub>CC</sub> = 2.5 V ± 0.2 V

over operating free-air temperature range (unless otherwise noted)

		T <sub>A</sub> = 25°C		T <sub>A</sub> = -40°C TO 85°C		T <sub>A</sub> = -40°C TO 125°C		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
t <sub>w</sub>	Pulse duration	SRCLK high or low		7	7.5	8.5		ns
		RCLK high or low		7	7.5	8.5		
		SRCLR low		6	6.5	7.5		
t <sub>su</sub>	Setup time	SER before SRCLK ↑		5.5	5.5	6.5		ns
		SRCLK ↑ before RCLK ↑ <sup>(1)</sup>		8	9	10		
		SRCLR low before RCLK ↑		8.5	9.5	10.5		
		SRCLR high (inactive) before SRCLK ↑		4	4	5		
t <sub>h</sub>	Hold time	SER after SRCLK ↑		1.5	1.5	2.5		ns

- (1) This setup time allows the storage register to receive stable data from the shift register. The clocks can be tied together, in which case the shift register is one clock pulse ahead of the storage register.

## 6.7 Timing Requirements, $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$

over operating free-air temperature range (unless otherwise noted)

		$T_A = 25^\circ\text{C}$		$T_A = -40^\circ\text{C}$ TO $85^\circ\text{C}$		$T_A = -40^\circ\text{C}$ TO $125^\circ\text{C}$		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
$t_w$	Pulse duration	SRCLK high or low		5.5	5.5	6.5		ns
		RCLK high or low		5.5	5.5	6.5		
		SRCLR low		5	5	6		
$t_{su}$	Setup time	SER before SRCLK $\uparrow$		3.5	3.5	4.5		ns
		SRCLK $\uparrow$ before RCLK $\uparrow$ <sup>(1)</sup>		8	8.5	9.5		
		SRCLR low before RCLK $\uparrow$		8	9	10		
		SRCLR high (inactive) before SRCLK $\uparrow$		3	3	4		
$t_h$	Hold time	SER after SRCLK $\uparrow$		1.5	1.5	2.5		ns

- (1) This setup time allows the storage register to receive stable data from the shift register. The clocks can be tied together, in which case the shift register is one clock pulse ahead of the storage register.

## 6.8 Timing Requirements, $V_{CC} = 5\text{ V} \pm 0.5\text{ V}$

over operating free-air temperature range (unless otherwise noted)

		$T_A = 25^\circ\text{C}$		$T_A = -40^\circ\text{C}$ TO $85^\circ\text{C}$		$T_A = -40^\circ\text{C}$ TO $125^\circ\text{C}$		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
$t_w$	Pulse duration	SRCLK high or low		5	5	6		ns
		RCLK high or low		5	5	6		
		SRCLR low		5.2	5.2	6.2		
$t_{su}$	Setup time	SER before SRCLK $\uparrow$		3	3	4		ns
		SRCLK $\uparrow$ before RCLK $\uparrow$ <sup>(1)</sup>		5	5	6		
		SRCLR low before RCLK $\uparrow$		5	5	6		
		SRCLR high (inactive) before SRCLK $\uparrow$		2.5	2.5	3.5		
$t_h$	Hold time	SER after SRCLK $\uparrow$		2	2	3		ns

- (1) This setup time allows the storage register to receive stable data from the shift register. The clocks can be tied together, in which case the shift register is one clock pulse ahead of the storage register.

## 6.9 Switching Characteristics, $V_{CC} = 2.5\text{ V} \pm 0.2\text{ V}$

over recommended operating free-air temperature range,  $C_L = 50\text{ pF}$  (unless otherwise noted)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$T_A = 25^\circ\text{C}$			$T_A = -40^\circ\text{C}$ TO $85^\circ\text{C}$		$T_A = -40^\circ\text{C}$ TO $125^\circ\text{C}$		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
$f_{max}$			60	70		40		30		MHz
$t_{PLH}$	RCLK	$Q_A-Q_H$	11.2	17.2		1	19.3	1	22.3	ns
$t_{PHL}$			11.2	17.2		1	19.3	1	22.3	ns
$t_{PLH}$	SRCLK	$Q_H$	13.1	22.5		1	25.5	1	28.5	ns
$t_{PHL}$			13.1	22.5		1	25.5	1	28.5	ns
$t_{PHL}$	SRCLR	$Q_H$	12.4	18.8		1	21.1	1	24.1	ns
$t_{PZH}$	OE	$Q_A-Q_H$	10.8	17		1	18.3	1	21.3	ns
$t_{PZL}$			13.4	21		1	23	1	26	ns
$t_{PHZ}$	OE	$Q_A-Q_H$	12.2	18.3		1	19.5	1	22.5	ns
$t_{PLZ}$			14	20.9		1	22.6	1	25.6	ns

## 6.10 Switching Characteristics, $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$

over recommended operating free-air temperature range,  $C_L = 50\text{ pF}$  (unless otherwise noted)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$T_A = 25^\circ\text{C}$			$T_A = -40^\circ\text{C}$ TO $85^\circ\text{C}$		$T_A = -40^\circ\text{C}$ TO $125^\circ\text{C}$		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
$f_{\max}$			55	105		50		40		MHz
$t_{\text{PLH}}$	RCLK	$Q_A-Q_H$		7.9	15.4	1	17	1	20	ns
$t_{\text{PHL}}$				7.9	15.4	1	17	1	20	ns
$t_{\text{PLH}}$	SRCLK	$Q_{H'}$		9.2	16.5	1	18.5	1	21.5	ns
$t_{\text{PHL}}$				9.2	16.5	1	18.5	1	21.5	ns
$t_{\text{PHL}}$	$\overline{\text{SRCLR}}$	$Q_{H'}$		9	16.3	1	17.2	1	20.2	ns
$t_{\text{PZH}}$	$\overline{\text{OE}}$	$Q_A-Q_H$		7.8	15	1	17	1	20	ns
$t_{\text{PZL}}$				9.6	15	1	17	1	20	ns
$t_{\text{PHZ}}$	$\overline{\text{OE}}$	$Q_A-Q_H$		8.1	15.7	1	16.2	1	19.2	ns
$t_{\text{PLZ}}$				9.3	15.7	1	16.2	1	19.2	ns

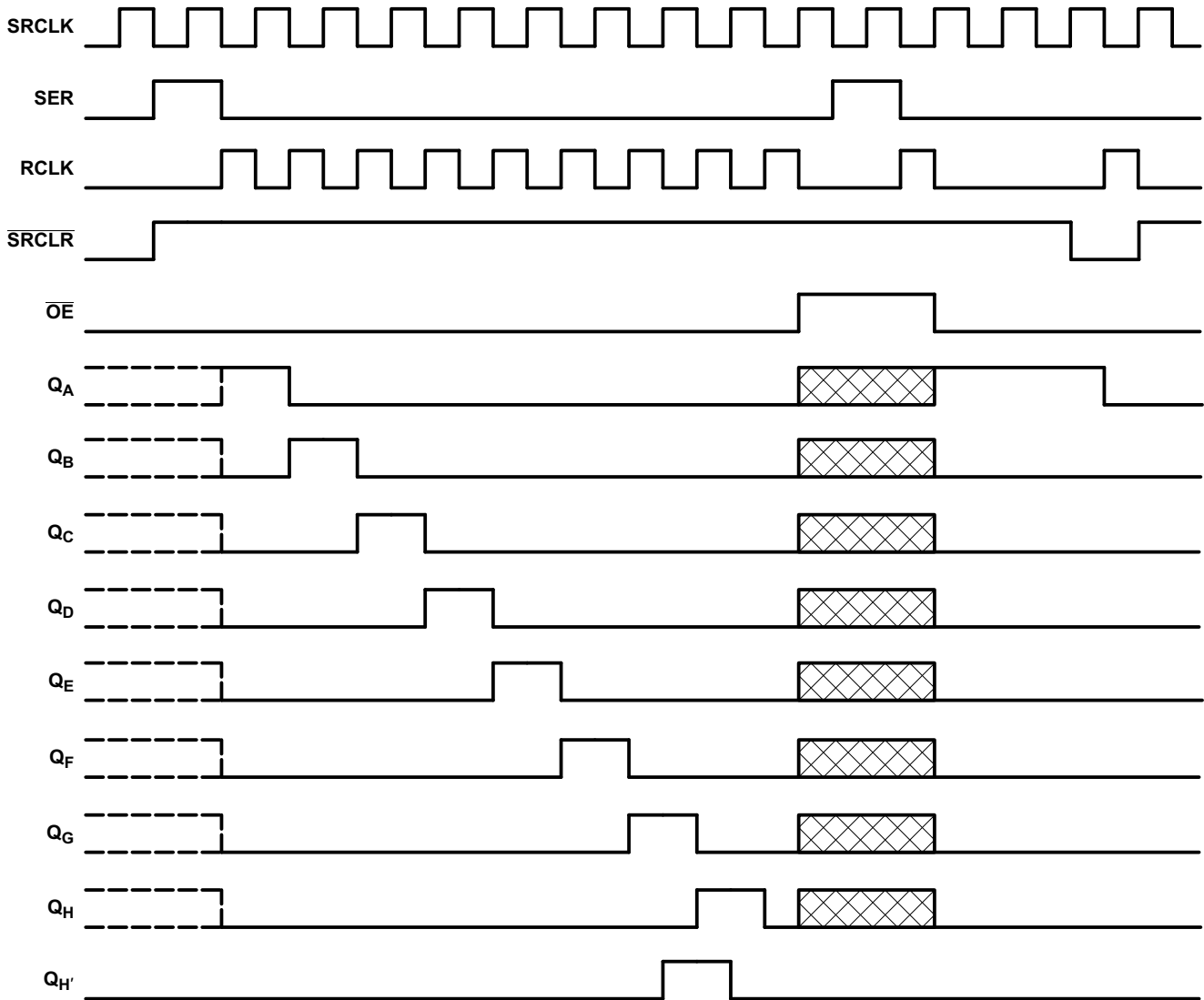
## 6.11 Switching Characteristics, $V_{CC} = 5\text{ V} \pm 0.5\text{ V}$

over recommended operating free-air temperature range,  $C_L = 50\text{ pF}$  (unless otherwise noted)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$T_A = 25^\circ\text{C}$			$T_A = -40^\circ\text{C}$ TO $85^\circ\text{C}$		$T_A = -40^\circ\text{C}$ TO $125^\circ\text{C}$		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
$f_{\max}$			95	140		85		75		MHz
$t_{\text{PLH}}$	RCLK	$Q_A-Q_H$		5.6	9.4	1	10.5	1	13.5	ns
$t_{\text{PHL}}$				5.6	9.4	1	10.5	1	13.5	ns
$t_{\text{PLH}}$	SRCLK	$Q_{H'}$		6.4	10.2	1	11.4	1	14.4	ns
$t_{\text{PHL}}$				6.4	10.2	1	11.4	1	14.4	ns
$t_{\text{PHL}}$	$\overline{\text{SRCLR}}$	$Q_{H'}$		6.4	10	1	11.1	1	14.1	ns
$t_{\text{PZH}}$	$\overline{\text{OE}}$	$Q_A-Q_H$		5.7	10.6	1	12	1	15	ns
$t_{\text{PZL}}$				6.8	10.6	1	12	1	15	ns
$t_{\text{PHZ}}$	$\overline{\text{OE}}$	$Q_A-Q_H$		3.5	10.3	1	11	1	14	ns
$t_{\text{PLZ}}$				3.4	10.3	1	11	1	14	ns



## 6.12 Timing Diagrams



NOTE:  implies that the output is in 3-State mode.

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图 6-1. Timing Diagram

## 6.13 Noise Characteristics

$V_{CC} = 3.3\text{ V}$ ,  $C_L = 50\text{ pF}$ ,  $T_A = 25^\circ\text{C}^{(1)}$

PARAMETER		MIN	TYP	MAX	UNIT
$V_{OL(P)}$	Quiet output, maximum dynamic $V_{OL}$		0.3		V
$V_{OL(V)}$	Quiet output, minimum dynamic $V_{OL}$		-0.2		V
$V_{OH(V)}$	Quiet output, minimum dynamic $V_{OH}$		2.8		V
$V_{IH(D)}$	High-level dynamic input voltage	2.31			V
$V_{IL(D)}$	Low-level dynamic input voltage			0.99	V

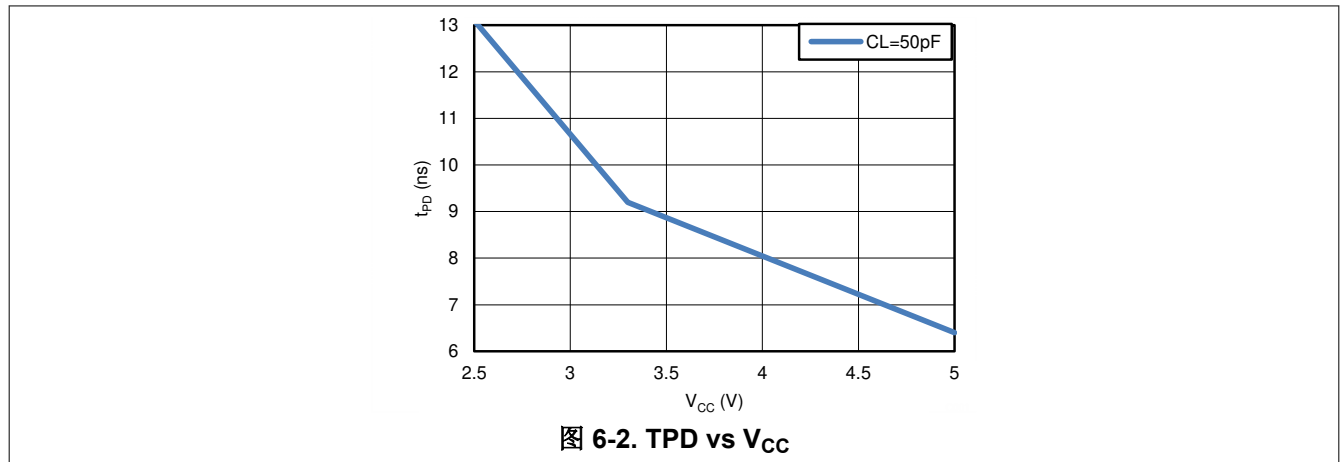
(1) Characteristics are for surface-mount packages only.

### 6.14 Operating Characteristics

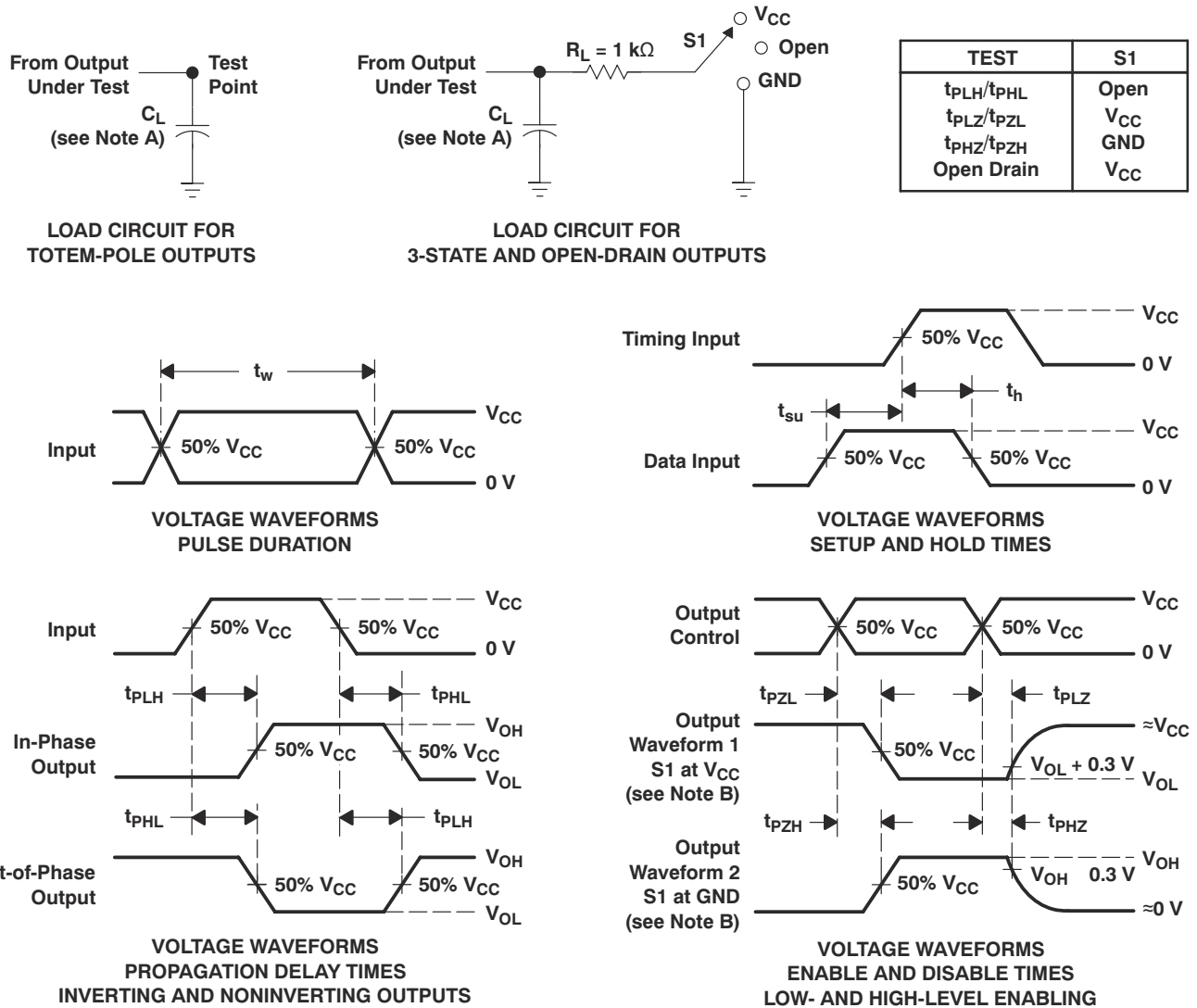
T<sub>A</sub> = 25°C

PARAMETER		TEST CONDITIONS	TYP	UNIT	
C <sub>pd</sub>	Power dissipation capacitance	C <sub>L</sub> = 50 pF, f = 10 MHz	V <sub>CC</sub> = 3.3 V	111	pF
			V <sub>CC</sub> = 5 V	114	

### 6.15 Typical Characteristics



## 7 Parameter Measurement Information



- NOTES:
- A.  $C_L$  includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
  - C. All input pulses are supplied by generators having the following characteristics:  $PRR \leq 1\text{ MHz}$ ,  $Z_O = 50\ \Omega$ ,  $t_r \leq 3\text{ ns}$ ,  $t_f \leq 3\text{ ns}$ .
  - D. The outputs are measured one at a time, with one input transition per measurement.
  - E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
  - F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
  - G.  $t_{PHL}$  and  $t_{PLH}$  are the same as  $t_{pd}$ .
  - H. All parameters and waveforms are not applicable to all devices.

图 7-1. Load Circuit and Voltage Waveforms

## 8 Detailed Description

### 8.1 Overview

The SN74LV595A-Q1 contains an 8-bit serial-in, parallel-out shift register that feeds an 8-bit D-type storage register. The storage register has parallel 3-state outputs. Separate clocks are provided for both the shift and storage register. The shift register has a direct overriding clear ( $\overline{\text{SRCLR}}$ ) input, serial (SER) input, and a serial output for cascading. When the output-enable ( $\overline{\text{OE}}$ ) input is high, all outputs except  $Q_H$  are in the high-impedance state.

Both the shift register clock (SRCLK) and storage register clock (RCLK) are positive-edge triggered. If both clocks are connected together, the shift register always is one clock pulse ahead of the storage register.

To ensure the high-impedance state during power up or power down,  $\overline{\text{OE}}$  should be tied to  $V_{CC}$  through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The device is fully specified for partial-power-down applications using  $I_{off}$ . The  $I_{off}$  circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

### 8.2 Functional Block Diagram

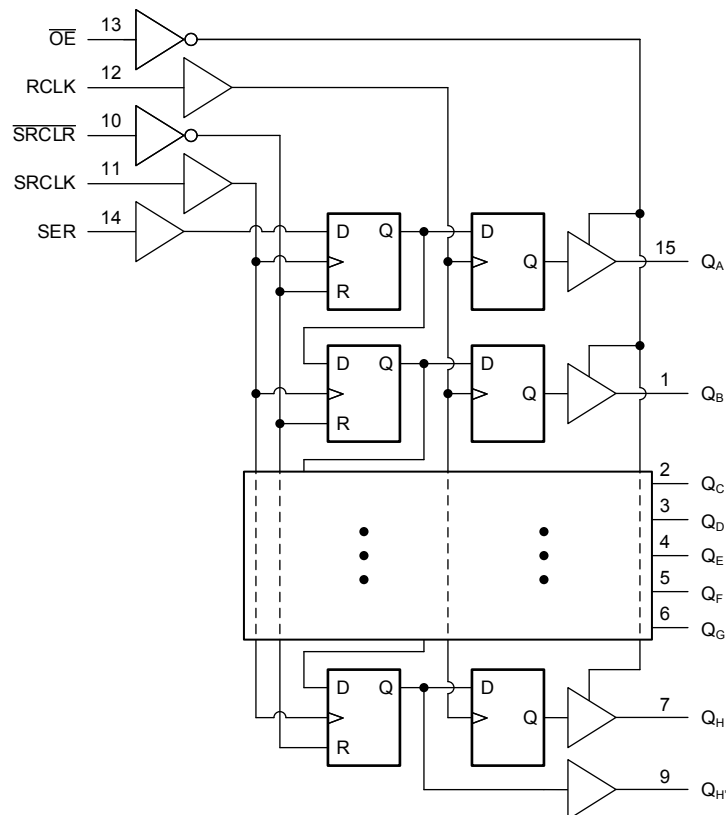


图 8-1. Logic Diagram (Positive Logic)

## 8.3 Feature Description

### 8.3.1 Balanced CMOS 3-State Outputs

This device includes balanced CMOS 3-state outputs. Driving high, driving low, and high impedance are the three states that these outputs can be in. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device can drive larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

When placed into the high-impedance mode, the output will neither source nor sink current, with the exception of minor leakage current as defined in the *Electrical Characteristics* table. In the high-impedance state, the output voltage is not controlled by the device and is dependent on external factors. If no other drivers are connected to the node, then this is known as a floating node and the voltage is unknown. A pull-up or pull-down resistor can be connected to the output to provide a known voltage at the output while it is in the high-impedance state. The value of the resistor will depend on multiple factors, including parasitic capacitance and power consumption limitations. Typically, a 10-k $\Omega$  resistor can be used to meet these requirements.

Unused 3-state CMOS outputs should be left disconnected.

### 8.3.2 Latching Logic

This device includes latching logic circuitry. Latching circuits commonly include D-type latches and D-type flip-flops, but include all logic circuits that act as volatile memory.

When the device is powered on, the state of each latch is unknown. There is no default state for each latch at start-up.

The output state of each latching logic circuit only remains stable as long as power is applied to the device within the supply voltage range specified in the *Recommended Operating Conditions* table.

### 8.3.3 Partial Power Down ( $I_{off}$ )

This device includes circuitry to disable all outputs when the supply pin is held at 0 V. When disabled, the outputs will neither source nor sink current, regardless of the input voltages applied. The amount of leakage current at each output is defined by the  $I_{off}$  specification in the *Electrical Characteristics* table.

### 8.3.4 Wettable Flanks

This device includes wettable flanks for at least one package. See the *Features* section on the front page of the data sheet for which packages include this feature.

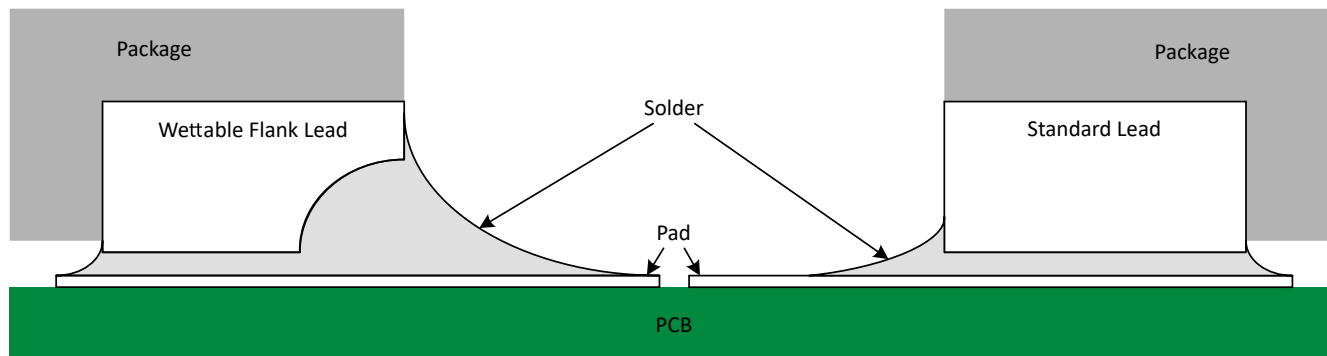


图 8-2. Simplified Cutaway View of Wettable-Flank QFN Package and Standard QFN Package After Soldering

Wettable flanks help improve side wetting after soldering, which makes QFN packages easier to inspect with automatic optical inspection (AOI). As shown in 图 8-2, a wettable flank can be dimpled or step-cut to provide additional surface area for solder adhesion which assists in reliably creating a side fillet. Please see the mechanical drawing for additional details.

### 8.3.5 Clamp Diode Structure

图 8-3 shows the inputs and outputs to this device have negative clamping diodes only.

**CAUTION**

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

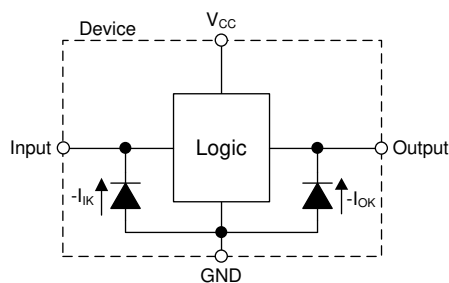


图 8-3. Electrical Placement of Clamping Diodes for Each Input and Output

## 8.4 Device Functional Modes

**表 8-1. Function Table**

INPUTS <sup>(1)</sup>					FUNCTION
SER	SRCLK	SRCLR	RCLK	OE	
X	X	X	X	H	Outputs Q <sub>A</sub> –Q <sub>H</sub> are disabled. Q <sub>H</sub> remains enabled.
X	X	X	X	L	Outputs Q <sub>A</sub> –Q <sub>H</sub> are enabled.
X	X	L	X	X	Shift register is cleared.
L	↑	H	X	X	First stage of the shift register goes low. Other stages store the data of previous stage, respectively.
H	↑	H	X	X	First stage of the shift register goes high. Other stages store the data of previous stage, respectively.
X	X	X	↑	X	Shift-register data is stored in the storage register.

(1) H = High Voltage Level, L = Low Voltage Level, X = Do not Care, Z = High Impedance

## 9 Application and Implementation

### 备注

以下应用部分中的信息不属于 TI 器件规格的范围，TI 不担保其准确性和完整性。TI 的客户应负责确定器件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

### 9.1 Application Information

The SN74LV595A-Q1 is a low-drive CMOS device that can be used for a multitude of bus interface type applications where output ringing is a concern. The low drive and slow edge rates will minimize overshoot and undershoot on the outputs. The inputs are 5-V tolerant allowing for down translation to  $V_{CC}$ .

### 9.2 Typical Application

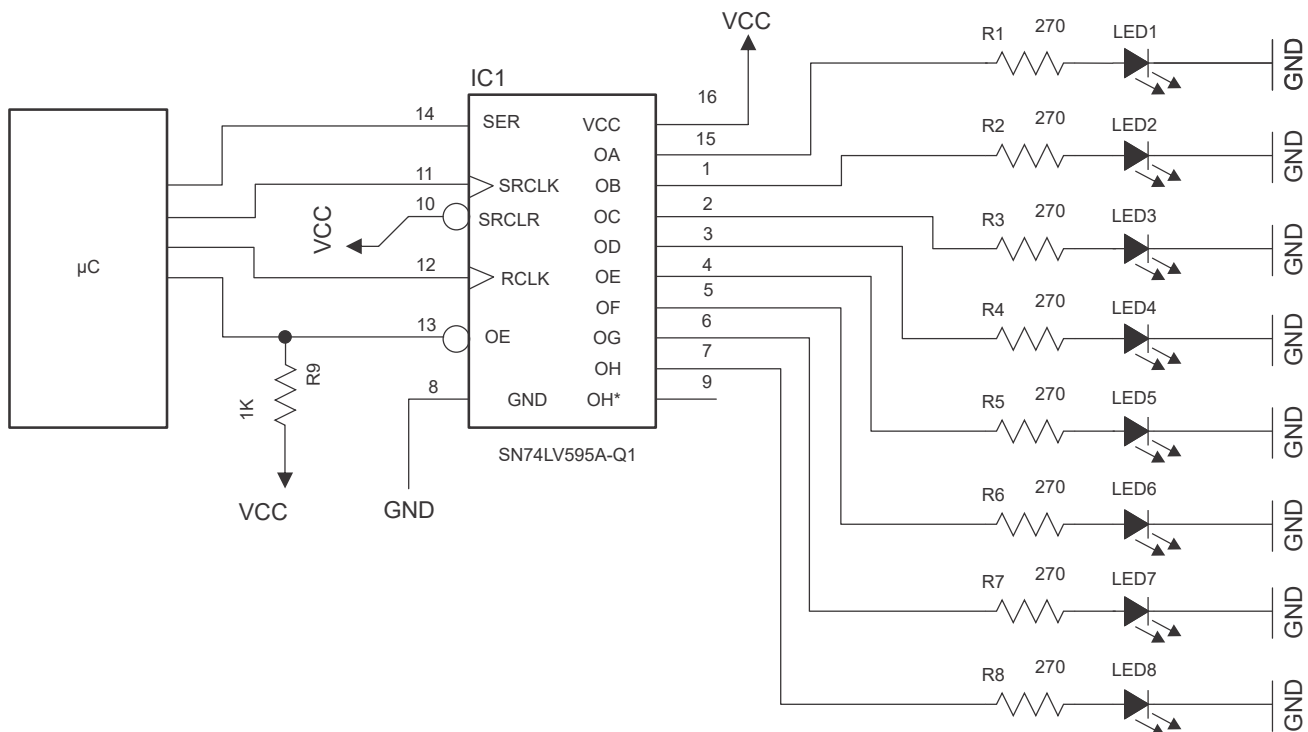


图 9-1. SN74LV595A-Q1 Expanding IOs to Drive LEDs

#### 9.2.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74LV595A-Q1 plus the maximum static supply current,  $I_{CC}$ , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only source as much current that is provided by the positive supply source. Be sure to not exceed the maximum total current through  $V_{CC}$  listed in the *Absolute Maximum Ratings*.



The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74LV595A-Q1 plus the maximum supply current,  $I_{CC}$ , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current that can be sunk into its ground connection. Be sure to not exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

The SN74LV595A-Q1 can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50 pF.

The SN74LV595A-Q1 can drive a load with total resistance described by  $R_L \geq V_O / I_O$ , with the output voltage and current defined in the *Electrical Characteristics* table with  $V_{OH}$  and  $V_{OL}$ . When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the  $V_{CC}$  pin.

Total power consumption can be calculated using the information provided in [CMOS Power Consumption and Cpd Calculation](#).

Thermal increase can be calculated using the information provided in [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices](#).

#### CAUTION

The maximum junction temperature,  $T_{J(max)}$  listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

### 9.2.2 Input Considerations

Input signals must cross  $V_{IL(max)}$  to be considered a logic LOW, and  $V_{IH(min)}$  to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either  $V_{CC}$  or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN74LV595A-Q1 (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A 10-k $\Omega$  resistor value is often used due to these factors.

The SN74LV595A-Q1 has CMOS inputs and thus requires fast input transitions to operate correctly, as defined in the *Recommended Operating Conditions* table. Slow input transitions can cause oscillations, additional power consumption, and reduction in device reliability.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

### 9.2.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the  $V_{OH}$  specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the  $V_{OL}$  specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to  $V_{CC}$  or ground.

Refer to the *Feature Description* section for additional information regarding the outputs for this device.

### 9.2.4 Detailed Design Procedure

1. Add a decoupling capacitor from  $V_{CC}$  to GND. The capacitor needs to be placed physically close to the device and electrically close to both the  $V_{CC}$  and GND pins. An example layout is shown in the *Layout* section.
2. Ensure the capacitive load at the output is  $\leq 50$  pF. This is not a hard limit; it will, however, ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74LV595A-Q1 to one or more of the receiving devices.
3. Ensure the resistive load at the output is larger than  $(V_{CC} / I_{O(max)}) \Omega$ . This will ensure that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in  $M\Omega$ ; much larger than the minimum calculated previously.
4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, [CMOS Power Consumption and Cpd Calculation](#).

### 9.2.5 Application Curves

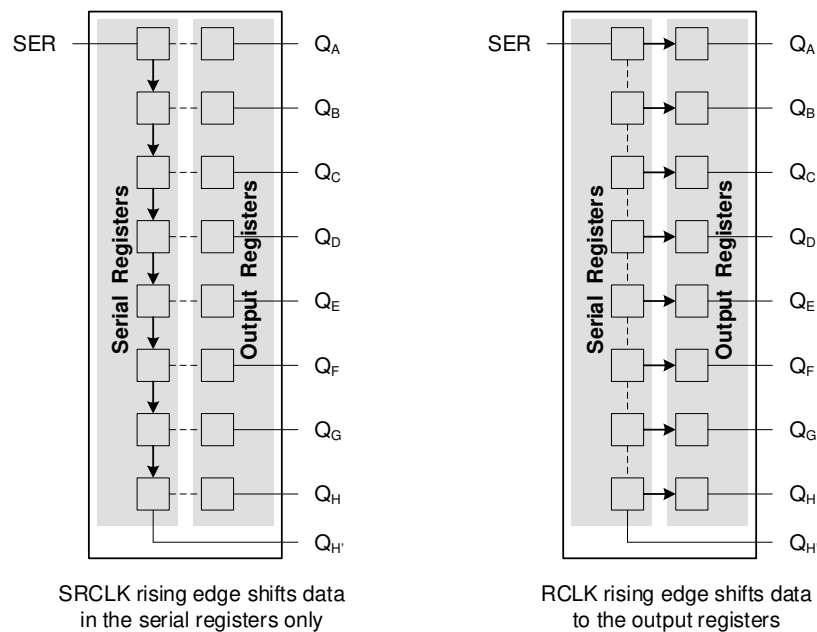


图 9-2. Simplified Functional Diagram Showing Clock Operation

### 9.3 Power Supply Recommendations

The power supply can be any voltage between the MIN and MAX supply voltage rating located in the [Recommended Operating Conditions](#) table.

Each  $V_{CC}$  terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a  $0.1 \mu\text{F}$  capacitor is recommended. If there are multiple  $V_{CC}$  terminals then  $0.01 \mu\text{F}$  or  $0.022 \mu\text{F}$  capacitors are recommended for each power terminal. It is ok to parallel multiple bypass capacitors to reject different frequencies of noise.  $0.1 \mu\text{F}$  and  $1.0 \mu\text{F}$  capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for the best results.

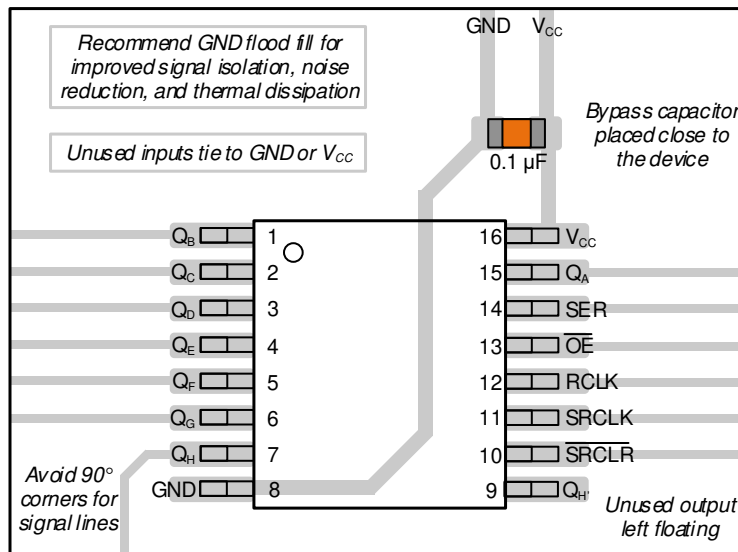
### 9.4 Layout

#### 9.4.1 Layout Guidelines

When using multiple bit logic devices, inputs should not float. In many cases, functions or parts of functions of digital logic devices are unused. Some examples are when only two inputs of a triple-input AND gate are used, or when only 3 of the 4-buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states.

Specified in [Figure 9-3](#) are rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or  $V_{CC}$ , whichever makes more sense or is more convenient. It is acceptable to float outputs unless the part is a transceiver. If the transceiver has an output enable pin, it will disable the outputs section of the part when asserted. This will not disable the input section of the I/Os so they also cannot float when disabled.

#### 9.4.2 Layout Example



**图 9-3. Layout Example for the SN74LV595A-Q1**

## 10 Device and Documentation Support

### 10.1 Documentation Support

#### 10.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [CMOS Power Consumption and Cpd Calculation application report](#)
- Texas Instruments, [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices application report](#)

#### 10.2 接收文档更新通知

要接收文档更新通知，请导航至 [ti.com](https://www.ti.com) 上的器件产品文件夹。点击 [订阅更新](#) 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

#### 10.3 支持资源

TI E2E™ [支持论坛](#) 是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的 [《使用条款》](#)。

#### 10.4 Trademarks

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#### 10.5 静电放电警告



静电放电 (ESD) 会损坏这个集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

#### 10.6 术语表

[TI 术语表](#) 本术语表列出并解释了术语、首字母缩略词和定义。

## 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LV595AIPWRG4Q1	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LV595AI	<a href="#">Samples</a>
SN74LV595AIPWRQ1	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 85	LV595AI	<a href="#">Samples</a>
SN74LV595AQPWRQ1	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV595AQ	<a href="#">Samples</a>
SN74LV595AQWBQBRQ1	ACTIVE	WQFN	BQB	16	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV595Q	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

**Important Information and Disclaimer:**The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and

continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

**OTHER QUALIFIED VERSIONS OF SN74LV595A-Q1 :**

- Catalog : [SN74LV595A](#)
- Enhanced Product : [SN74LV595A-EP](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product
- Enhanced Product - Supports Defense, Aerospace and Medical Applications

**TAPE AND REEL INFORMATION**

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LV595AIPWRG4Q1	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LV595AIPWRQ1	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LV595AQPWRQ1	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LV595AQWBQRQ1	WQFN	BQB	16	3000	180.0	12.4	2.8	3.8	1.2	4.0	12.0	Q1

**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LV595AIPWRG4Q1	TSSOP	PW	16	2000	356.0	356.0	35.0
SN74LV595AIPWRQ1	TSSOP	PW	16	2000	356.0	356.0	35.0
SN74LV595AQPWRQ1	TSSOP	PW	16	2000	356.0	356.0	35.0
SN74LV595AQWBQRQ1	WQFN	BQB	16	3000	210.0	185.0	35.0





4220204/A 02/2017

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

# EXAMPLE BOARD LAYOUT

PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE: 10X



SOLDER MASK DETAILS

4220204/A 02/2017

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

PW0016A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL  
SCALE: 10X

4220204/A 02/2017

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

## GENERIC PACKAGE VIEW

**BQB 16**

**WQFN - 0.8 mm max height**

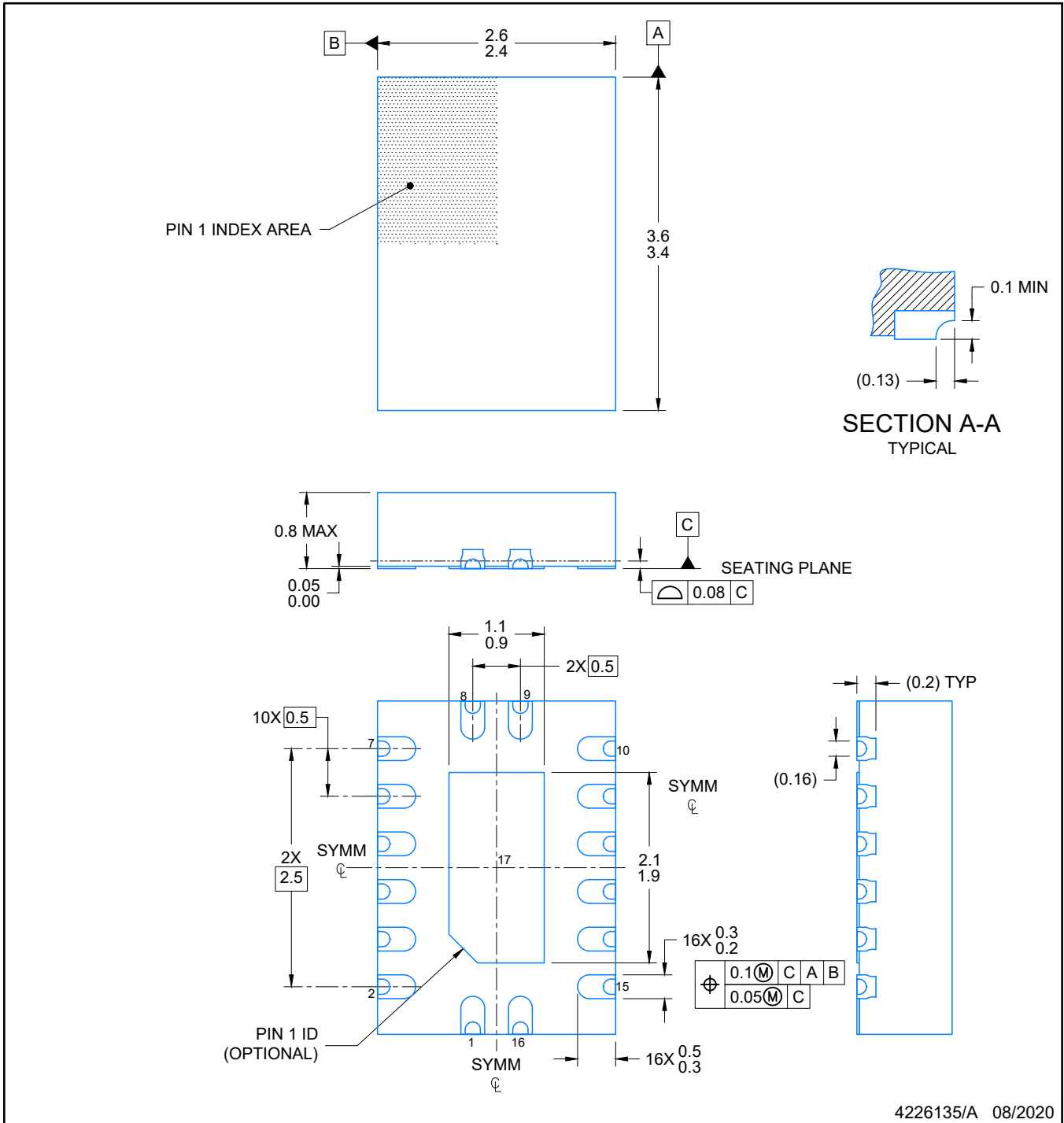
2.5 x 3.5, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary.  
Refer to the product data sheet for package details.



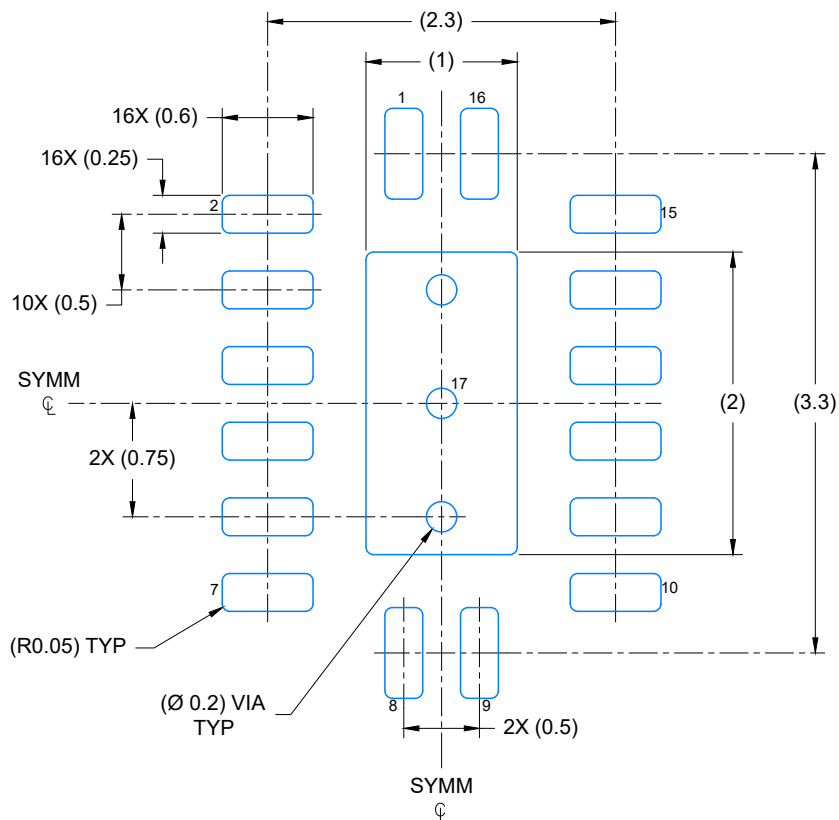
4226161/A



4226135/A 08/2020

**NOTES:**

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.

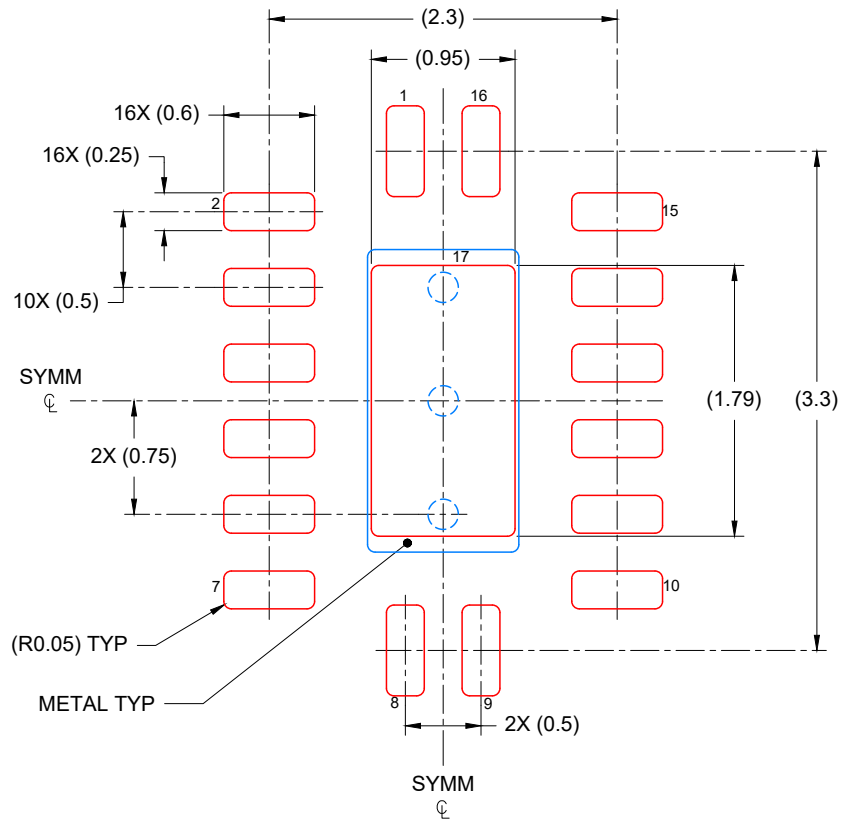


LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE: 20X

4226135/A 08/2020

NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 ([www.ti.com/lit/sluea271](http://www.ti.com/lit/sluea271)).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



SOLDER PASTE EXAMPLE  
 BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD  
 85% PRINTED COVERAGE BY AREA  
 SCALE: 20X

4226135/A 08/2020

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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